SHEET 1 OF 1

SERIAL NO. ATTY DOCKET NO. U.S. DEPARTMENT OF COMMERCE Form PTO 1449 " ibyten PATENT AND TRADEMARK OFFICE (Modified) 240416US0DIV 10/618,085 **APPLICANT** LIST OF REFERENCES CITED BY APPLICANT Masakazu KANECHIKA, et al. **GROUP FILING DATE** 2813 July 14, 2003 **U.S. PATENT DOCUMENTS EXAMINER** DOCUMENT SUB **FILING DATE CLASS** DATE NAME NUMBER **CLASS** IF APPROPRIATE INITIAL AA AB AC AD AE **AF** AG AH Αl AJ AK AL AM AN **FOREIGN PATENT DOCUMENTS DOCUMENT TRANSLATION** COUNTRY DATE **NUMBER** YES NO JP8-306752 JAPAN (with English Abstract) AO 11-22-96 AP JP7-118100 05-09-95 JAPAN (with English Abstract) JP8-203863 JAPAN (with English Abstract) AQ 08-09-96 JP9-232482 09-05-97 JAPAN (with English Abstract) AR AS **AT** AU ΑV OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.) Hayakawa et al; "Mechanism of Residue Formation in Silicon Trench Etching Using a Bromine-Based Plasma," Jpn. J. Appl. AW Phys., Vol. 37 (1998) pp. 5-9. AX AY ΑZ Additional References sheet(s) attached Examiner Nousen Date Considered \*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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